

Abstracts

High-Power X-Band MIC Diode Phase Shifters

S. Kamihashi, M. Kuroda and K. Hirai. "High-Power X-Band MIC Diode Phase Shifters." 1980 MTT-S International Microwave Symposium Digest 80.1 (1980 [MWSYM]): 81-83.

High-power X-band MIC diode phase shifters have been developed using glass-passivated PIN diodes with a grooved-mesa structure. Although they have outer dimensions of 20mm x 41mm x 10mm, they can handle 300W and 500W peak rf power depending upon the diodes used.

 [Return to main document.](#)